

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

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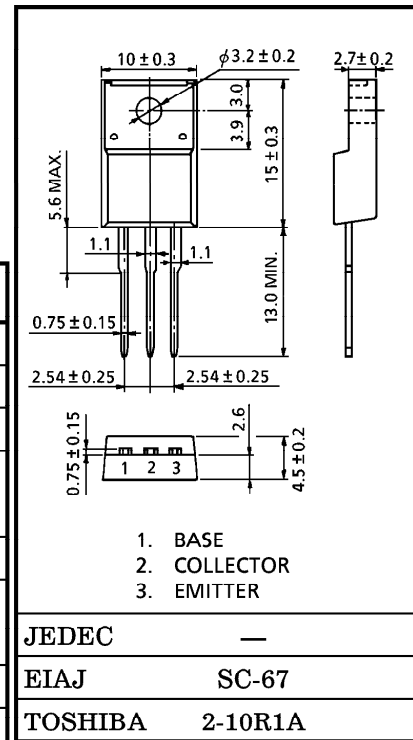
POWER AMPLIFIER APPLICATIONS

Unit in mm

- High DC Current Gain : $h_{FE} = 800 \sim 3200$
- Low Collector Saturation Voltage : $V_{CE(sat)} = 0.4V$ (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	60	V
Collector-Emitter Voltage		V_{CEO}	60	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	3	A
	Pulse	I_{CP}	6	
Base Current		I_B	0.6	A
Collector Power Dissipation	Ta = 25°C	P_C	2	W
	Tc = 25°C		25	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

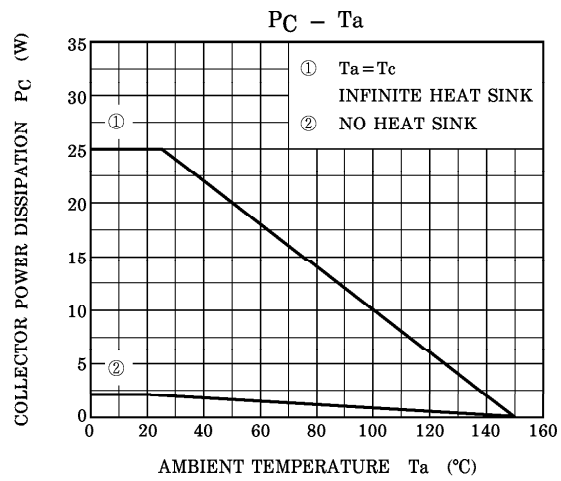
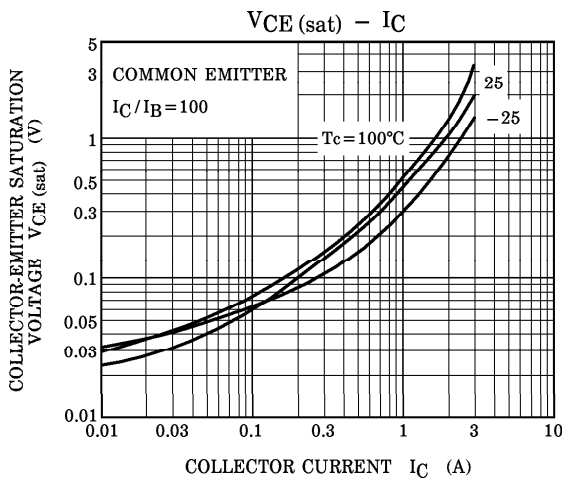
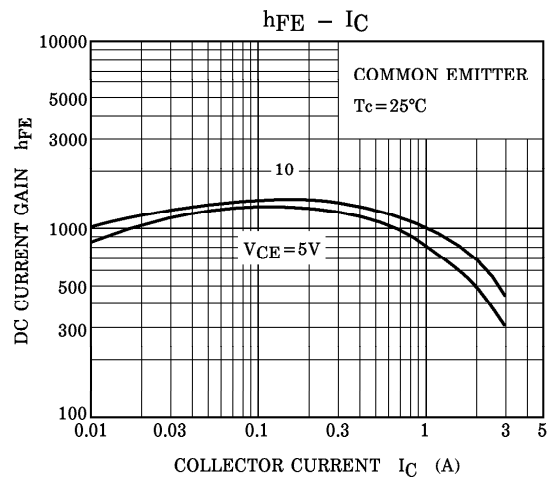
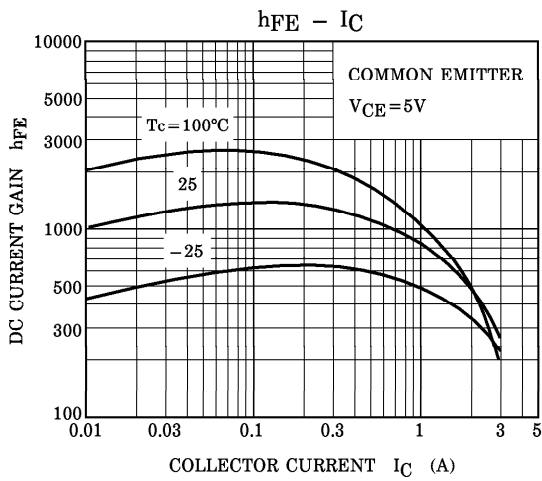
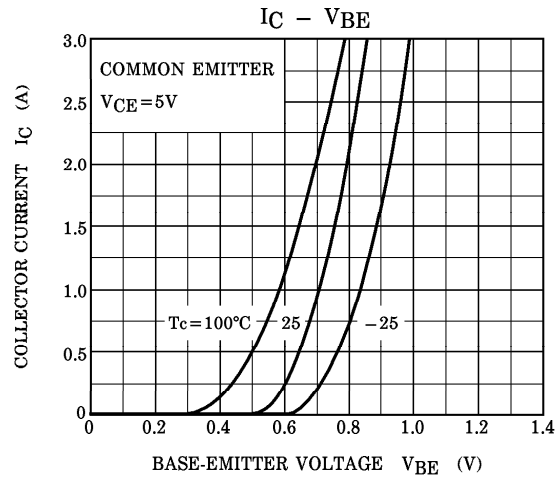
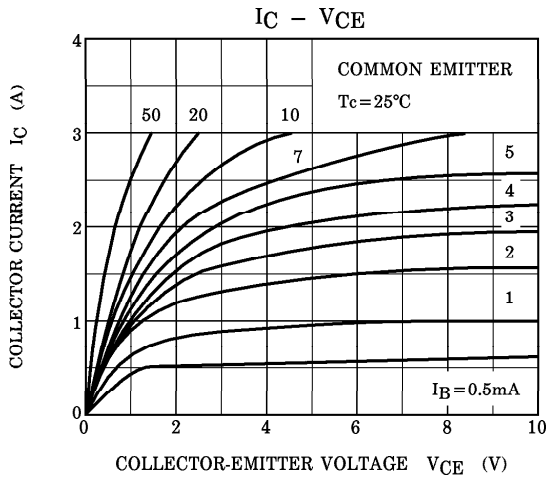


Weight : 1.7g (Typ.)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 60V, I_E = 0$	—	—	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 6V, I_C = 0$	—	—	100	μA
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C = 50mA, I_B = 0$	60	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5V, I_C = 0.2A$	800	—	3200	
	$h_{FE(2)}$	$V_{CE} = 5V, I_C = 1.5A$	350	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1A, I_B = 10mA$	—	0.4	1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5V, I_C = 0.5A$	—	0.7	1.0	V
Transition Frequency	f_T	$V_{CE} = 5V, I_C = 0.5A$	—	18	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	42	—	pF

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